

SAND2015-1300C

Device-Level Models Using Multi-Valley Effective Mass

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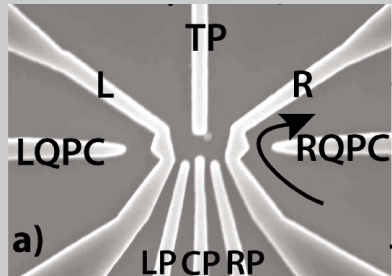
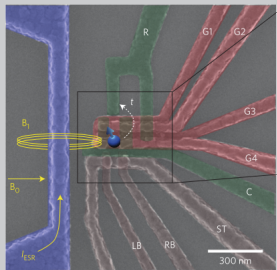
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► Collaborators:

- John King Gamble → G37.00007, full-scope modeling
- Toby Jacobson → W37.00009, open dynamics
- Adam Frees → W37.00010, donor-dot tunneling
- Everyone else → Xujiao (Suzey) Gao, John Mitchell, Inès Montañó, Rick Muller, and Erik Nielsen

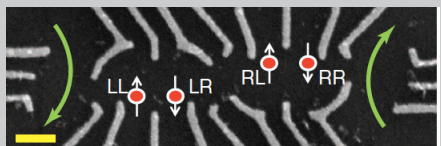
► Nomenclature:

- 2DEG → Two-Dimensional Electron Gas
- CI → Configuration Interaction
- DG → Discontinuous Galerkin
- DQD → Double Quantum Dot
- EMT → Effective Mass Theory
- FEM → Finite Element Method
- PDE → Partial Differential Equation
- QCAD → Quantum Computer Aided Design
- VO → Valley-Orbit



Veldhorst, et. al., *Nature Nano* (2014)

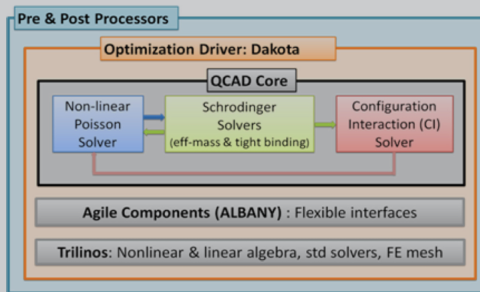
Nguyen, et. al., arXiv:1403.3704



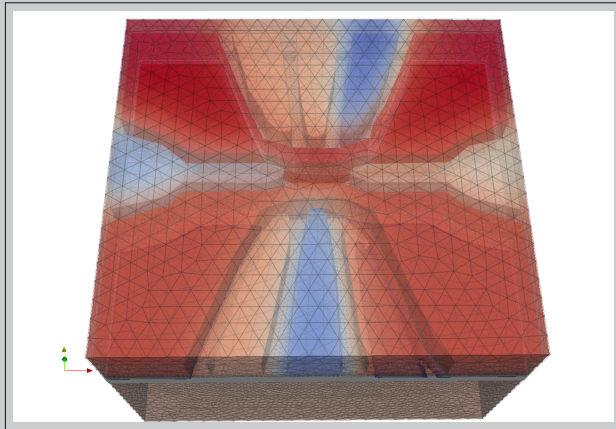
Shulman, et. al., *Science* (2012)

QCAD: Present Scope

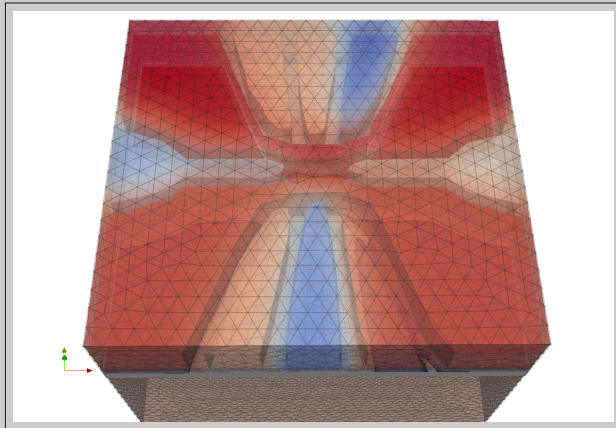
- ▶ SNL's self-consistent electrostatics / quantum package
- ▶ FEM discretization of PDEs
- ▶ See Gao, Nielsen, et. al., *J. App. Phys.*, 2013



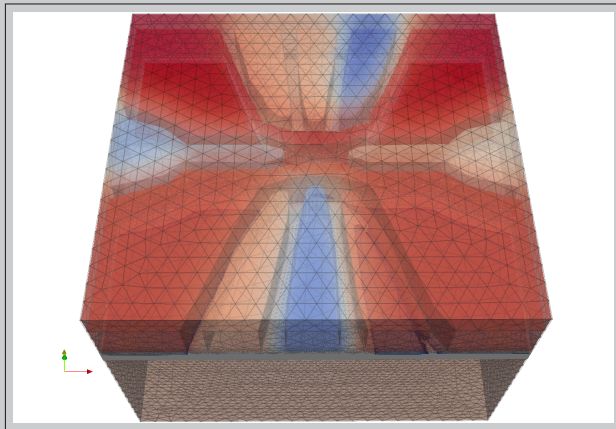
- ▶ **Currently:** strictly electrostatics, standard effective mass, and full-CI
- ▶ **Goal:** add physics to achieve high-fidelity model of qubit/environment
- ▶ **Problem:** more physics → complex solvers → high accuracy in solution



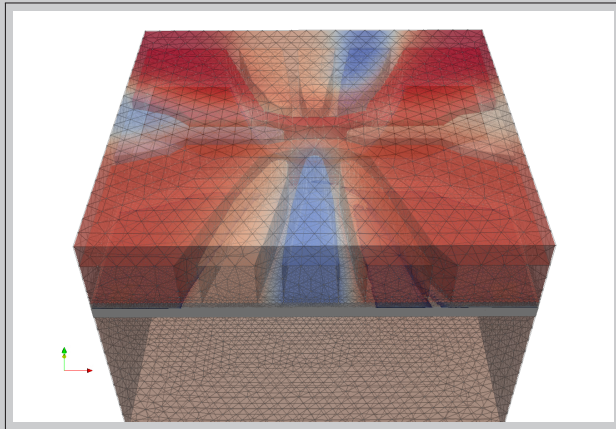
Red \rightarrow positive potential, blue \rightarrow negative potential
Domain size ~ 1.5 microns



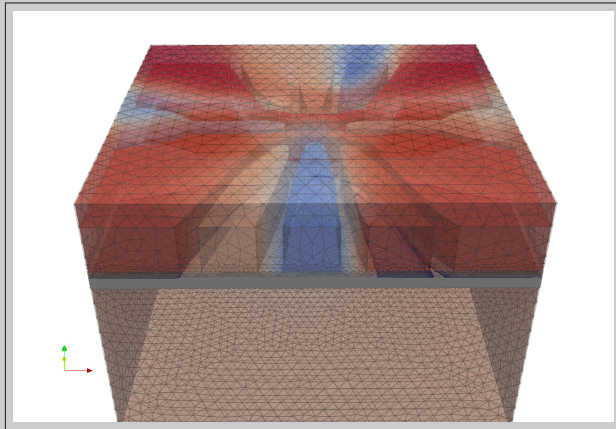
Largest edge length in gates ~ 75 nanometers



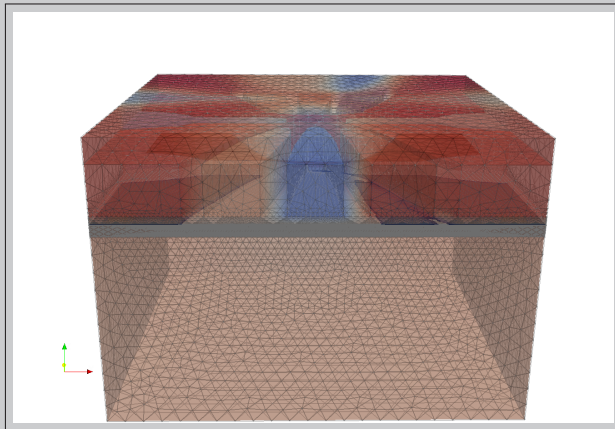
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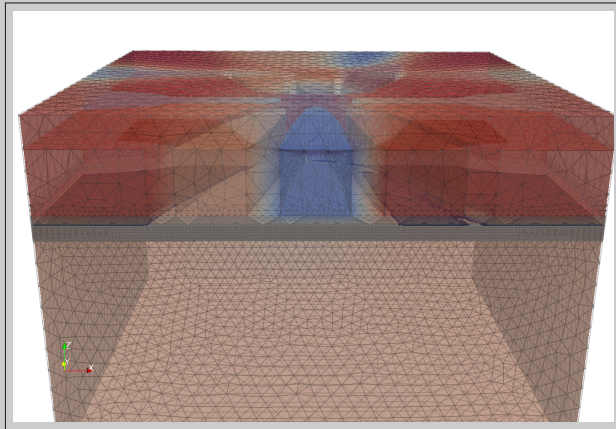
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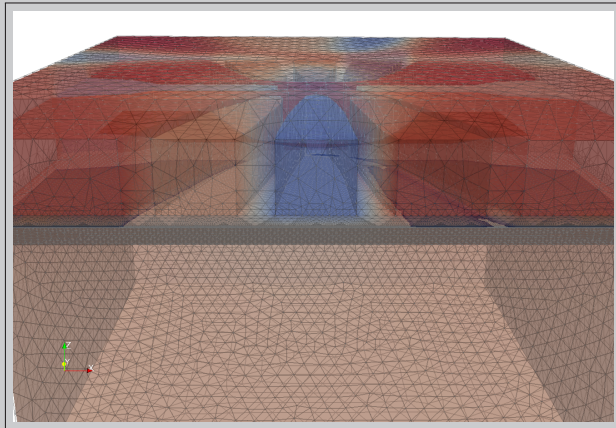
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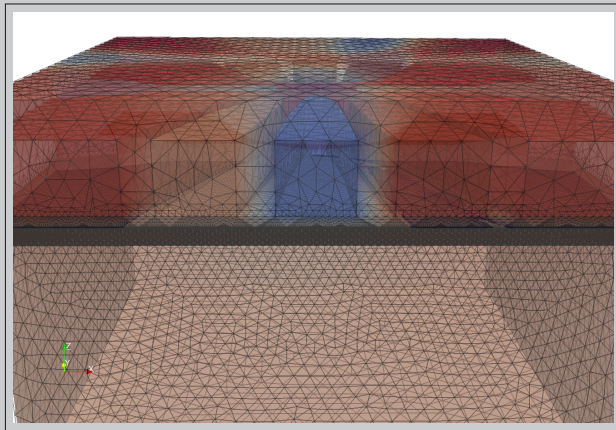
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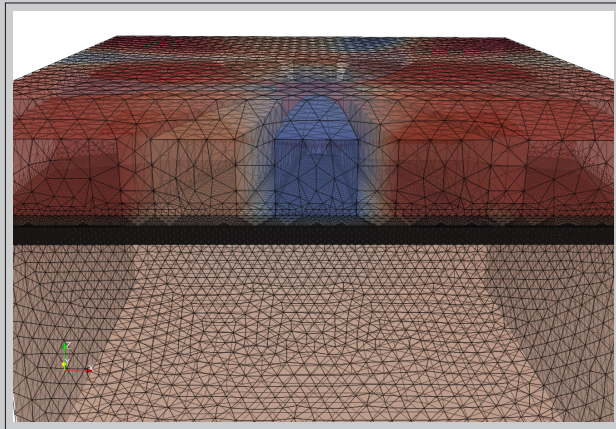
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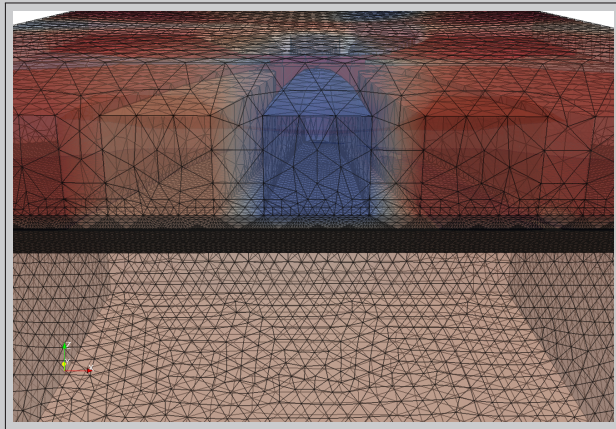
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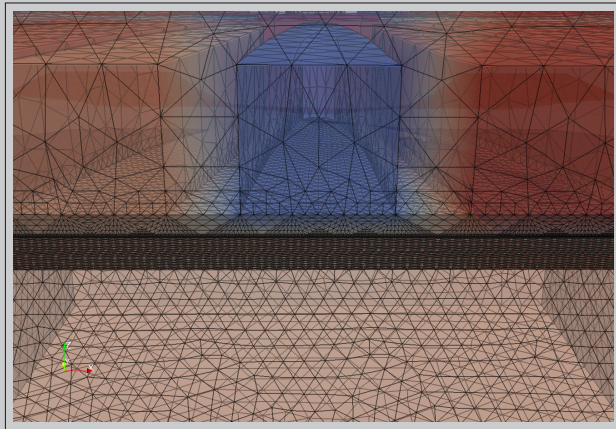
Approaching the 2DEG transition to ~ 20 nanometers



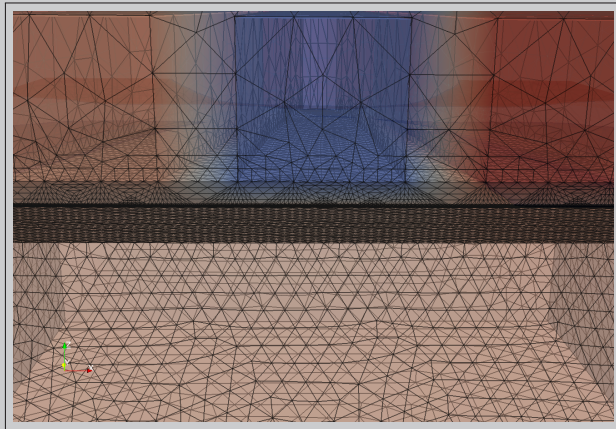
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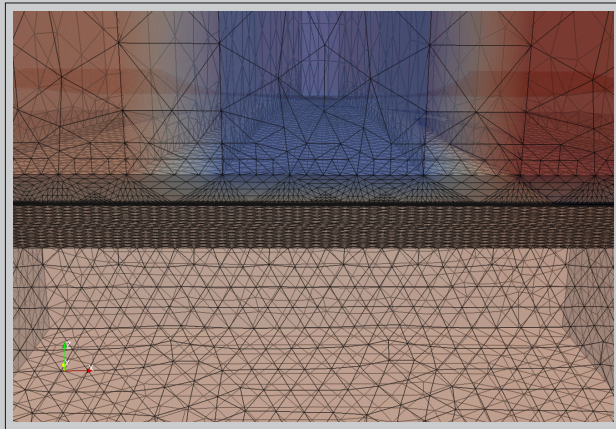
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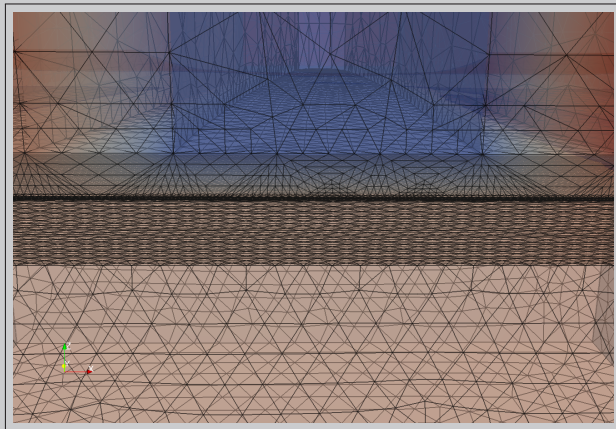
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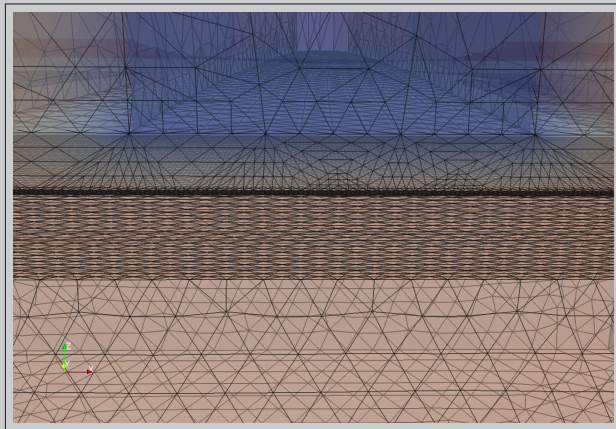
Down to ~ 5 nanometers



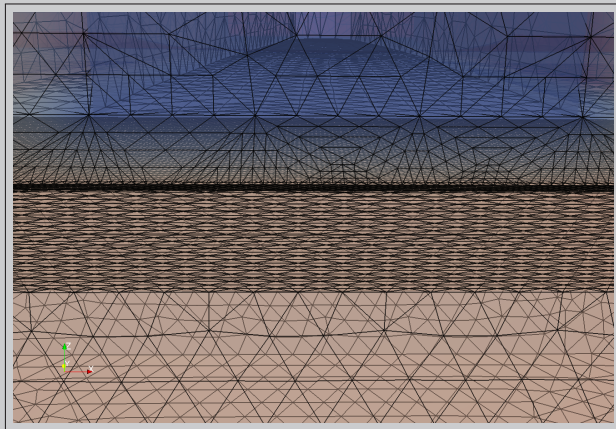
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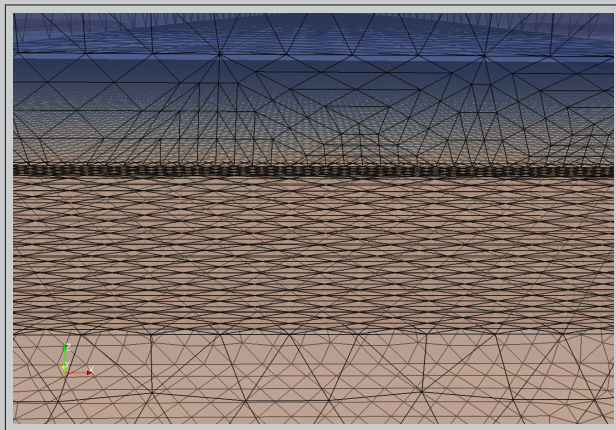
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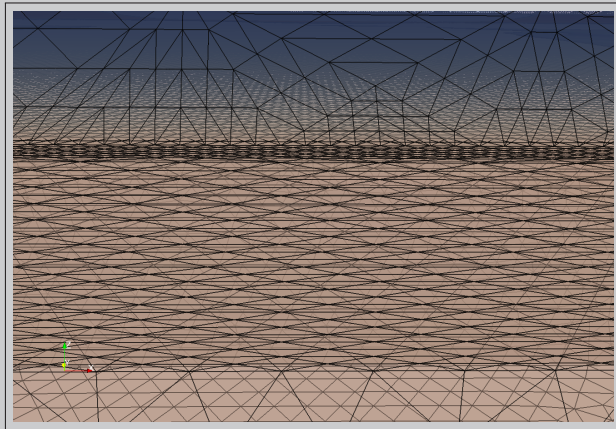
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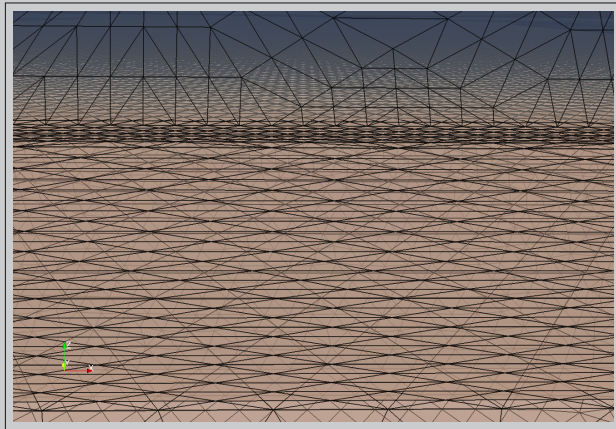
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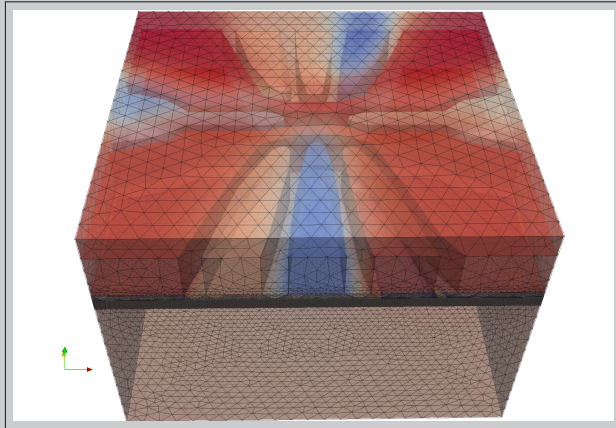
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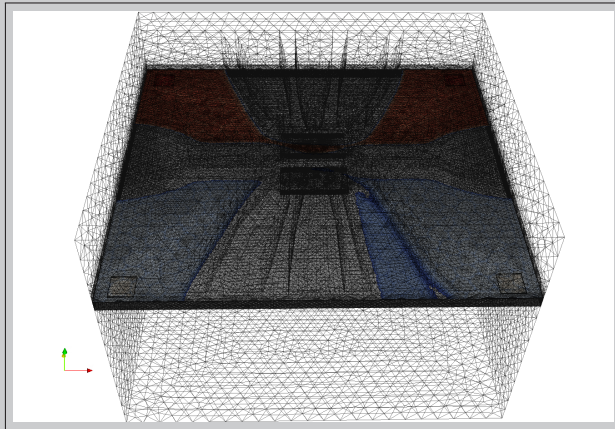
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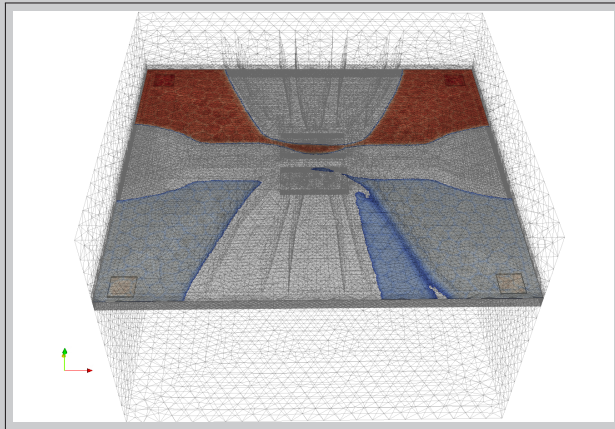
At the shortest scale is ~ 1 nanometer



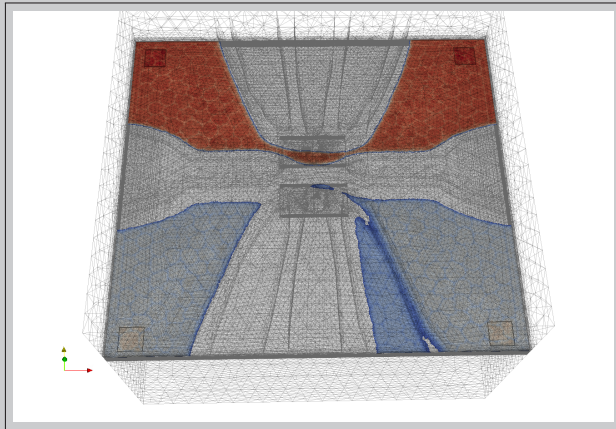
Looking at potential, level of refinement seems excessive. . .



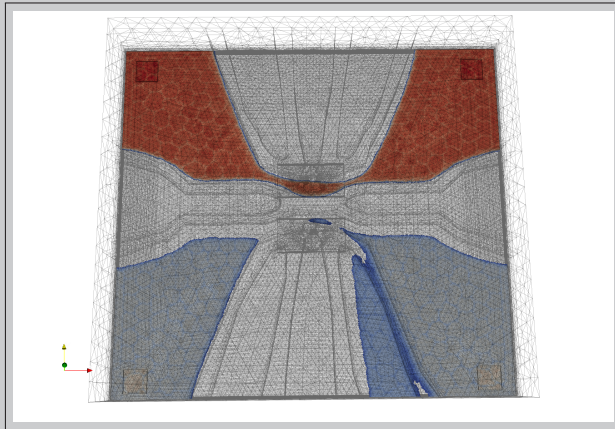
Looking at the electron density, we see why it is needed. . .



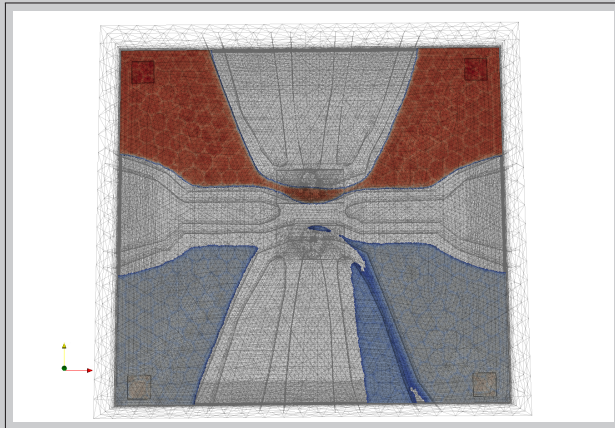
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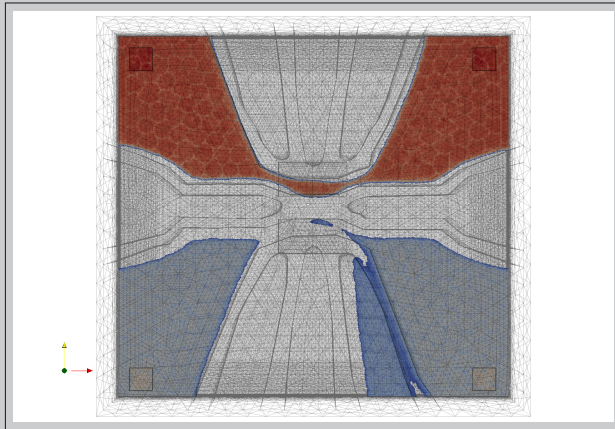
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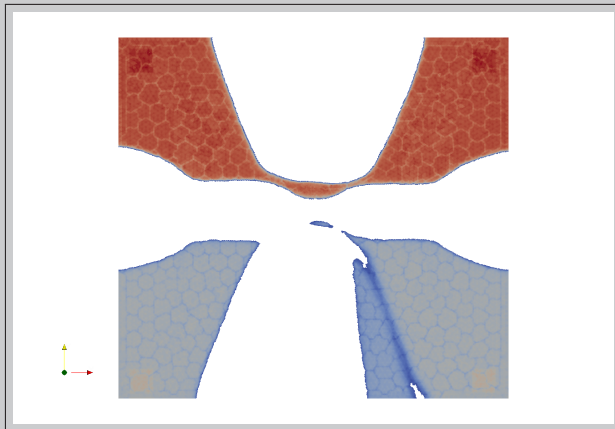
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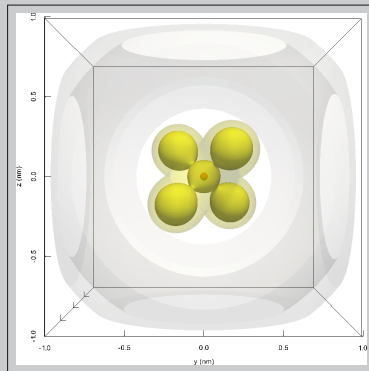


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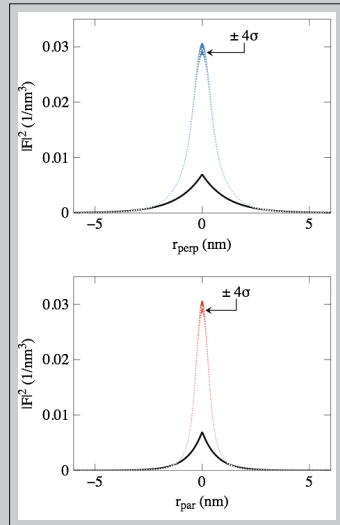
For a DQD device we need to resolve this 2DEG, working with donors/interfaces **we need to go the Angstrom scale**

- ▶ Angstrom-level physics included in multi-valley effective mass
- ▶ Recent work, Gamble/Jacobson, et. al. - [arXiv:1408.3159](https://arxiv.org/abs/1408.3159)
 - ▶ Tetrahedral central cell
 - ▶ Anisotropic Gaussian basis
 - ▶ First principles Bloch functions

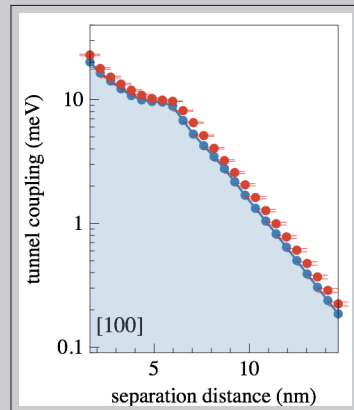


Multi-valley Effective Mass: Overview

- ▶ Angstrom-level physics included in multi-valley effective mass
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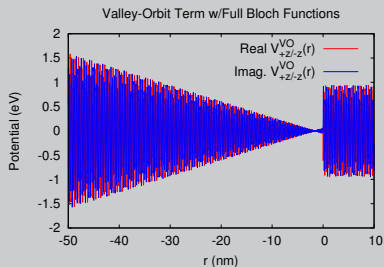
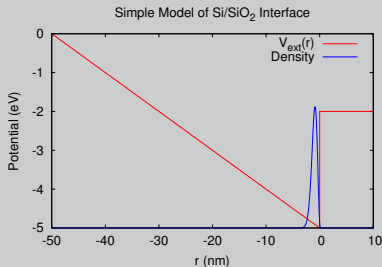


Multi-valley Effective Mass: Challenges

- Surprisingly difficult PDE: multi-scale, oscillatory coefficients

$$\left(-\frac{\hbar^2}{2} \nabla \cdot \bar{\bar{m}}(\mathbf{r})^{-1} \cdot \nabla + V_{\text{ext}}(\mathbf{r}) \right) F_j(\mathbf{r}) + \sum_{k \neq j} V_{jk}^{\text{VO}}(\mathbf{r}) F_k(\mathbf{r}) = E F_j(\mathbf{r})$$

$$V_{jk}^{\text{VO}}(\mathbf{r}) = \phi_j^*(\mathbf{r}) \phi_k^*(\mathbf{r}) V_{\text{ext}}(\mathbf{r})$$



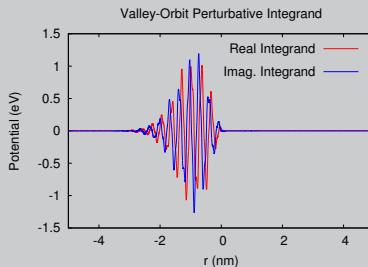
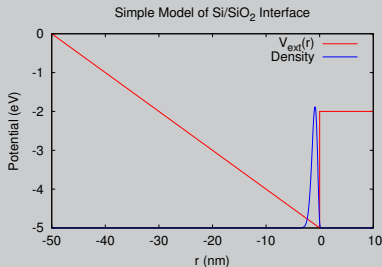
1D multi-valley EMT at interface inspired by Saraiva, et. al., PRB (2011)

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- ▶ **Goals:**

- ▶ Systematically improvable numerical method
- ▶ Efficient embedding into QCAD-like framework
- ▶ Amenable to interfacing with atomistics

What can we learn from engineers/applied mathematicians to solve difficult PDE-based models?

- ▶ Problems with resolution arise from **incomplete use of known physics**

“Physicist’s” variational basis

- ▶ Perturbation on solved problem
- ▶ Gaussians, Sturm-Liouville eigenfunctions, etc.
- ▶ Global support → dense
- ▶ Difficult to adapt
- ▶ Few degrees of freedom
- ▶ Boundary conditions?

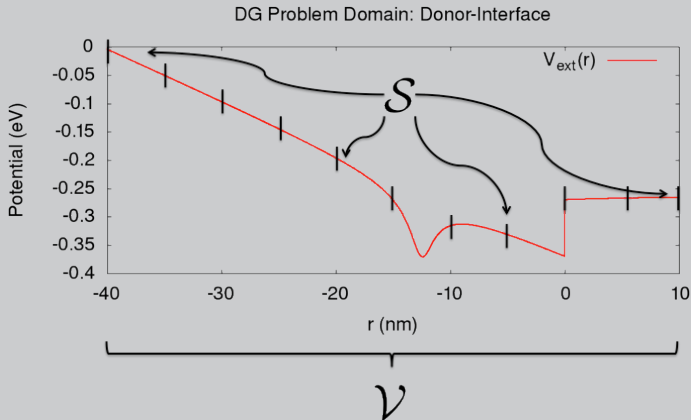
“Engineer’s” approach (e.g., FEM)

- ▶ Agnostic of problem instance
- ▶ Local polynomials, samples + stencil, etc.
- ▶ Compact support → sparse
- ▶ Natural adaptivity
- ▶ Many degrees of freedom
- ▶ Boundary conditions!

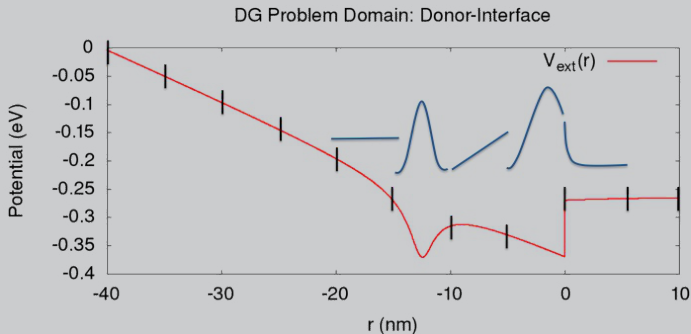
- ▶ **Features of both needed for full-scope/multi-scale problems**

Discontinuous Galerkin framework allows us to stitch together optimal solutions

1. Break **domain** (\mathcal{V}) into **sub-domains** with a set of **interfaces** (\mathcal{S})
2. Choose basis ($\{u_{j,k}\}$) for sub-domain k based upon **local physics**
3. **Weak soln.** of Schrödinger eqn. \rightarrow soln. of **variational problem**



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DG: Step-by-Step

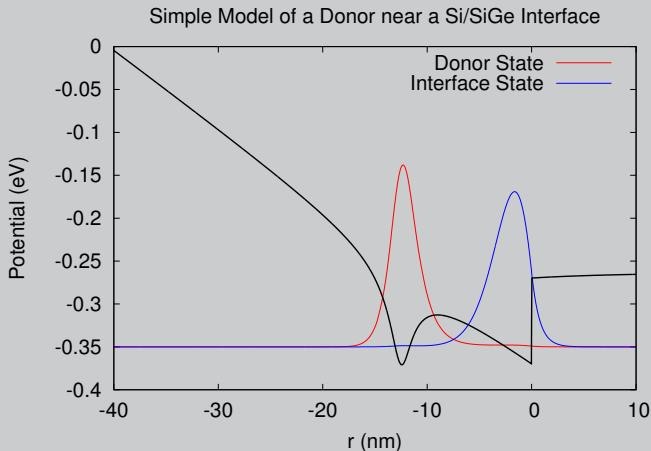
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Minimize $\mathcal{E}[\psi_i]$ for $\psi_i \in \text{span}\{u_{j,k}\} \rightarrow$ Euler-Lagrange **looks like** Schrödinger

$$\begin{aligned} \mathcal{E}[\psi_i] = & \frac{1}{2} \langle \nabla u_{j,k}, \nabla \psi_i \rangle_{\mathcal{V}} - \frac{1}{2} \langle \{\{\nabla u_{j,k}\}\}, [[\psi_i]] \rangle_{\mathcal{S}} - \frac{1}{2} \langle [[u_{j,k}]], \{\{\nabla \psi_i\}\} \rangle_{\mathcal{S}} \\ & + \frac{\alpha}{h} \langle [[u_{j,k}]], [[\psi_i]] \rangle_{\mathcal{S}} \langle u_{j,k}, V_{\text{ext}} \psi_i \rangle_{\mathcal{V}} = E_i \langle u_{j,k}, \psi_i \rangle_{\mathcal{V}} \end{aligned}$$

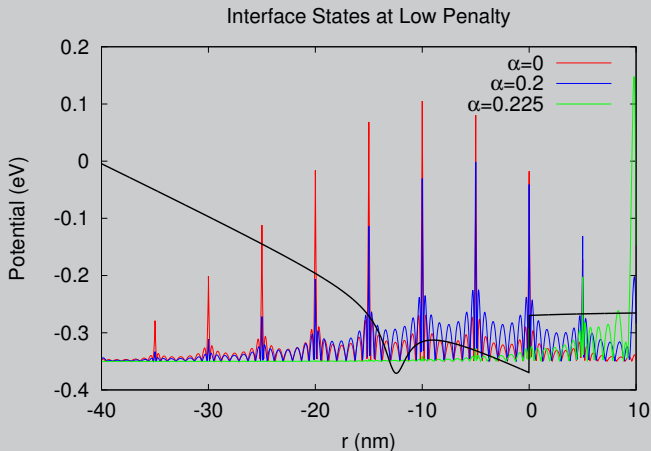
- **FEM**: arbitrary element of $\text{span}\{u_{j,k}\}$ is **continuous**
- **DG**: arbitrary element is **discontinuous** $\rightarrow \mathcal{E}[\psi_i]$ finds “continuous” ones

Solving for envelope states of interest:



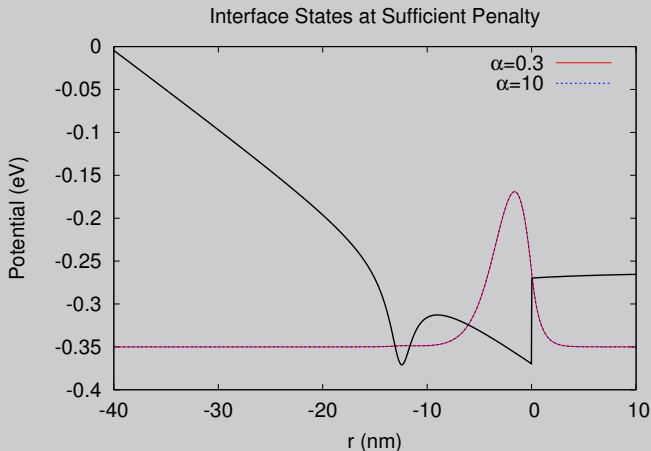
60 unknowns \rightarrow ground state and VO coupling to $\sim 0.01\%$

α parameter pushes pathological solutions to high energy



For small α we can see spurious discontinuous solutions

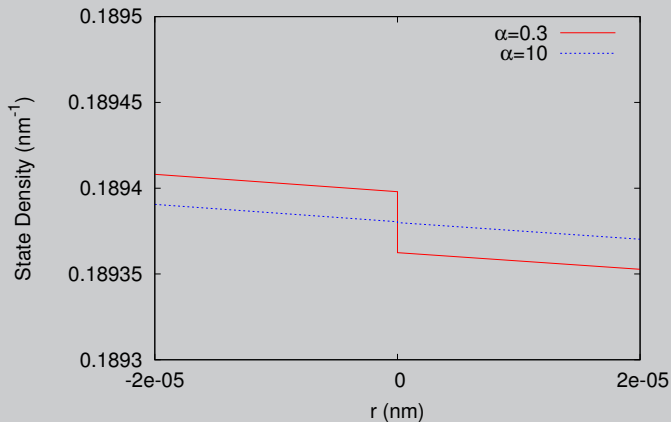
Parameter balances accuracy with conditioning



Large $\alpha \rightarrow$ small discontinuity, reduces diagonal dominance

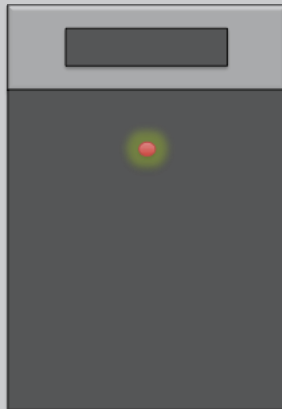
Discontinuity rigorously exists still

Close-Up Interface States at Sufficient Penalty

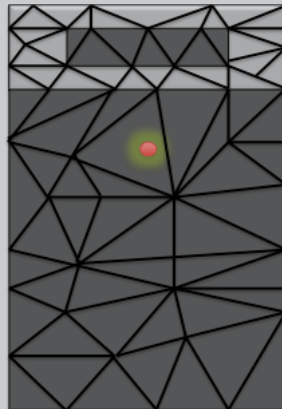


Controllable/negligible contribution to KE

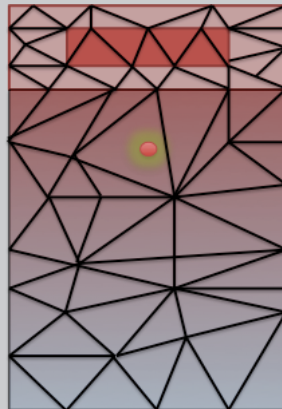
- ▶ Construct CAD model of device
- ▶ Build a coarse mesh for electrostatics
- ▶ Forward QCAD solve w/o VO physics
- ▶ Extract quantum region \rightarrow high order DG
- ▶ Local solvers adapt enriched basis



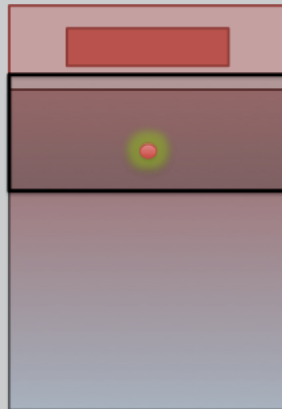
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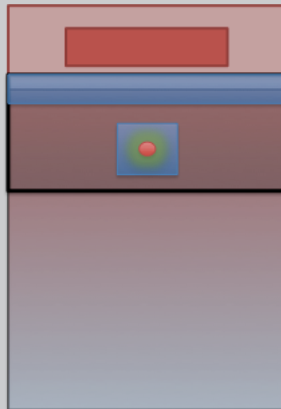
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► **Summary:**

- High fidelity numerical framework needed for complex models
- Multi-valley EMT is numerically challenging
- Discontinuous Galerkin methods are up to the challenge

► **Ongoing:**

- Implementation of full 3D capability
- Local adaptivity in space (and time)
- Projective model reduction-based dynamics (*stay for Toby's talk!*)

Thank you for your attention!